

Description

N-channel Enhancement Mode Power MOSFET

Features

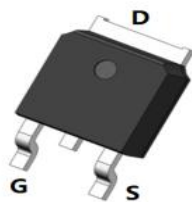
- 100V, 40A
 $R_{DS(ON)}$ Typ = 17m Ω @ V_{GS} = 10V
 $R_{DS(ON)}$ Typ = 18m Ω @ V_{GS} = 4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge

Applications

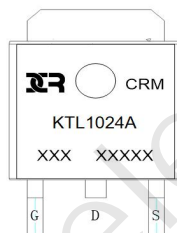
- Load Switch
- PWM Application
- Power Management



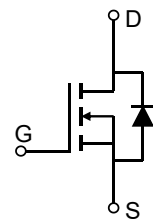
100% UIS TESTED!
100% ΔV_{ds} TESTED!



TO-252-3L



Marking and Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
CRMKTL1024A	CRMKTL1024A	TAPING	TO-252-3L	13"	2500	25000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
I_{DM}	Pulsed Drain Current ⁽¹⁾	160	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	121	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2	$^\circ\text{C/W}$
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$



Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.7	2.5	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = 10V, I _D = 20A	-	17.0	22.0	mΩ
		V _{GS} = 4.5V, I _D = 10A	-	18.0	24.0	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	5060	-	pF
C _{oss}	Output Capacitance		-	175	-	pF
C _{rss}	Reverse Transfer Capacitance		-	155	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 50V, I _D = 20A	-	101	-	nC
Q _{gs}	Gate Source Charge		-	26	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	24	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 50V I _D = 20A, R _{GEN} = 2.5Ω	-	20	-	ns
t _r	Turn-On Rise Time		-	24	-	ns
t _{d(off)}	Turn-Off DelayTime		-	45	-	ns
t _f	Turn-Off Fall Time		-	15	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	160	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 15A, di/dt = 100A/us	-	40	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	63	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=22A
 3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

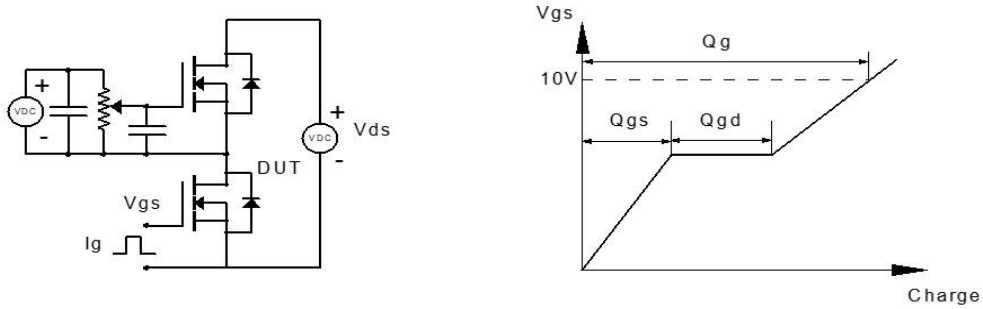


Figure 1: Gate Charge Test Circuit & Waveform

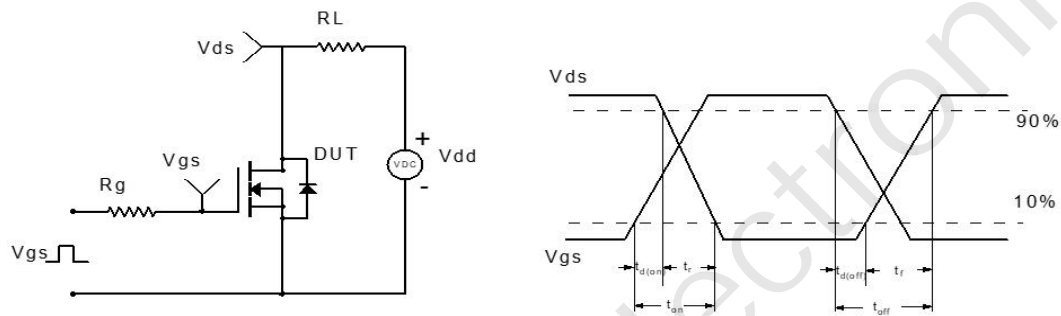


Figure 2: Resistive Switching Test Circuit & Waveform

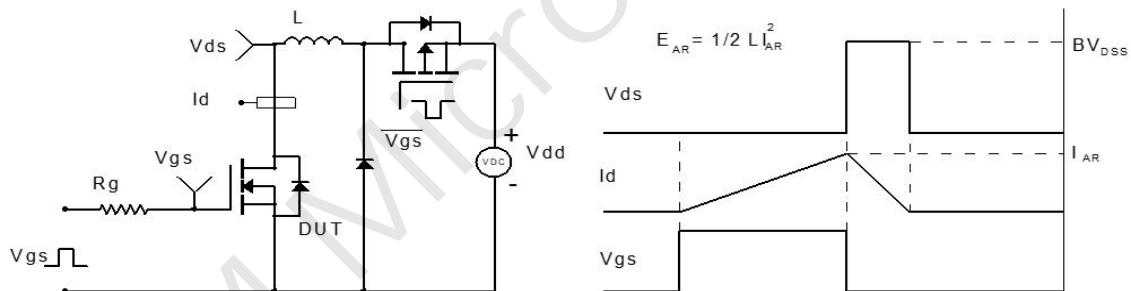


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

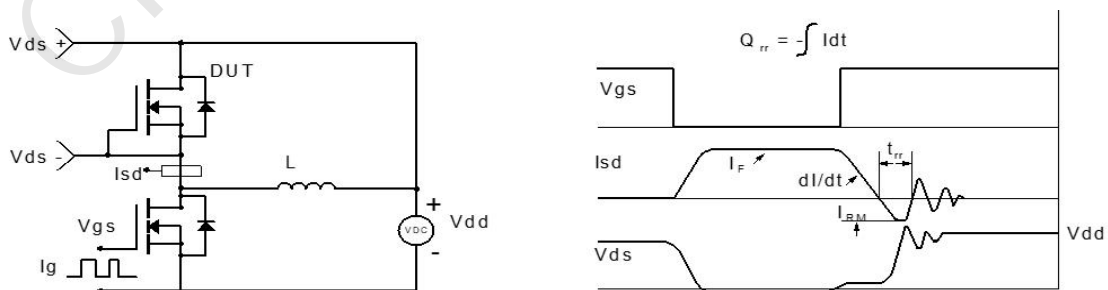
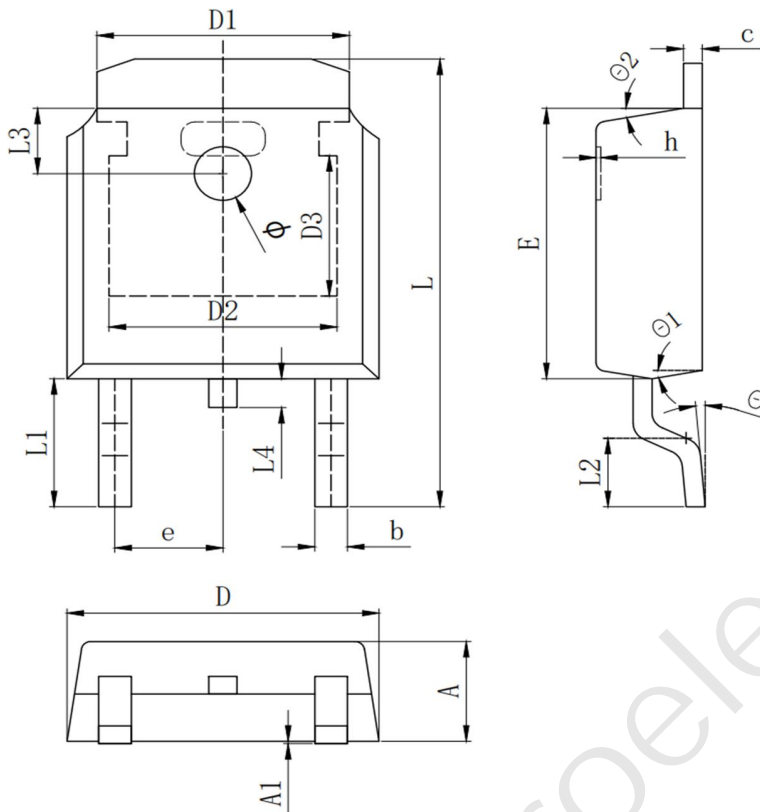


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-252-3L)



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c (电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
ϕ	1.100	1.200	1.300
θ	0°		8°
$\theta 1$	9° TYP		
$\theta 2$	9° TYP		

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